

Attorney Docket #10010872-1

Amendments to the Claims

This list of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-11 (Canceled)

12. (currently amended) A semiconductor device sloped via contact on a wafer having front and back sides, comprising:

a wafer of resistive semiconductor material, having a through hole, a front side, and a back side, wherein the width of the hole increases from a minimum width on one side to a maximum width on the other side;

a front contact on the front side of the wafer;

a back contact on the back side of the wafer; and

a metal layer that adheres to the inner walls of the through hole and connects the front contact to the back contact. a via through the wafer connecting the front contact to the back contact. , wherein

the via walls have a metal coating, and

the via increases in width.

13. (currently amended) The sloped via contact semiconductor device as in claim 12, wherein the via through hole is less than 80 microns at its widest.

14. (currently amended) The sloped via contact semiconductor device as in claim 13, wherein the via through hole is less than 50 microns at its widest.

15. (currently amended) The sloped via contact semiconductor device as in claim 13 wherein the metal coating layer on the via through hole is at least 1000 Angstroms thick where the via through hole is the narrowest.

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16. (currently amended) The ~~sloped-via-contact~~ semiconductor device as in claim 15, wherein the metal ~~coating~~ layer is selected from the group consisting of NiChrome and gold.

17. (currently amended) The ~~sloped-via-contact~~ semiconductor device as in claim 15, wherein the metal ~~coating~~ layer on the ~~via~~ through hole is partially plated.

18-20. (canceled)

21. (currently amended) The ~~sloped-via-contact~~ semiconductor device as in claim 13, wherein the slope of the ~~via~~ walls of the through hole is not constant.

22. (currently amended) The ~~sloped-via-contact~~ semiconductor device as in claim 13, wherein the ~~via~~ walls of the through hole are curved.